

### General Description

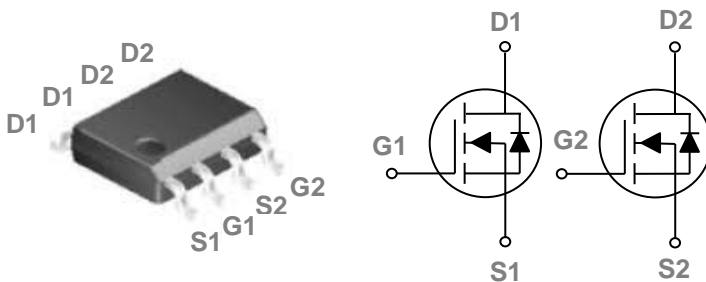
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R <sub>DS(ON)</sub>	I <sub>D</sub>
40V	15mΩ	10A

### Features

- 40V, 10A, R<sub>DS(ON)</sub> = 15mΩ @ V<sub>GS</sub> = 10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

### SOP8 Dual Pin Configuration



### Applications

- Motor Drive
- Power Tools
- LED Lighting

### Absolute Maximum Ratings T<sub>c</sub>=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	40	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>c</sub> =25°C)	10	A
	Drain Current – Continuous (T <sub>c</sub> =100°C)	6.3	A
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	40	A
EAS	Single Pulse Avalanche Energy <sup>2</sup>	76	mJ
IAS	Single Pulse Avalanche Current <sup>2</sup>	39	A
P <sub>D</sub>	Power Dissipation (T <sub>c</sub> =25°C)	2.1	W
	Power Dissipation – Derate above 25°C	0.017	W/°C
T <sub>STG</sub>	Storage Temperature Range	-50 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-50 to 150	°C

### Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	---	60	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	---	---	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	μA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =125°C	---	---	10	μA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	---	12	15	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	---	15	20	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250μA	1.2	1.8	2.5	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =1A	---	5	---	S

**Dynamic and switching Characteristics**

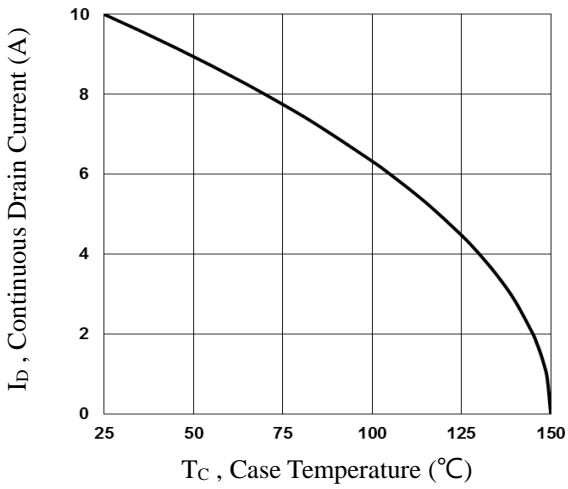
Q <sub>g</sub>	Total Gate Charge <sup>3,4</sup>	V <sub>DS</sub> =20V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	13	26	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>3,4</sup>		---	4	8	
Q <sub>gd</sub>	Gate-Drain Charge <sup>3,4</sup>		---	5.3	10	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>3,4</sup>	V <sub>DD</sub> =20V, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω I <sub>D</sub> =1A	---	8	16	ns
T <sub>r</sub>	Rise Time <sup>3,4</sup>		---	3.2	8	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>3,4</sup>		---	26.4	52	
T <sub>f</sub>	Fall Time <sup>3,4</sup>		---	3.8	8	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1MHz	---	1088	2000	pF
C <sub>oss</sub>	Output Capacitance		---	110	200	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	80	160	
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, F=1MHz	---	3	6	Ω

**Drain-Source Diode Characteristics and Maximum Ratings**

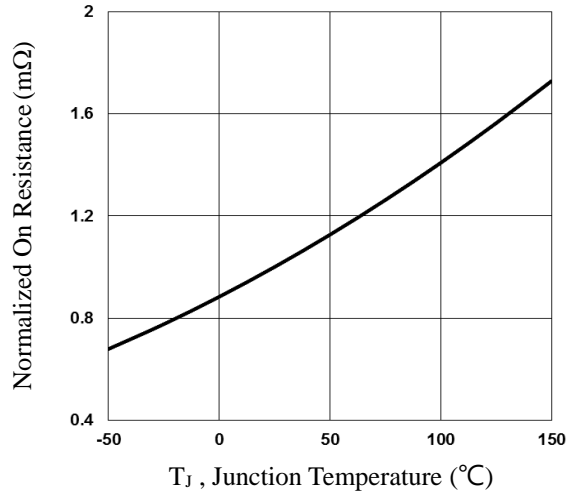
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	10	A
I <sub>SM</sub>	Pulsed Source Current		---	---	20	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1	V

Note :

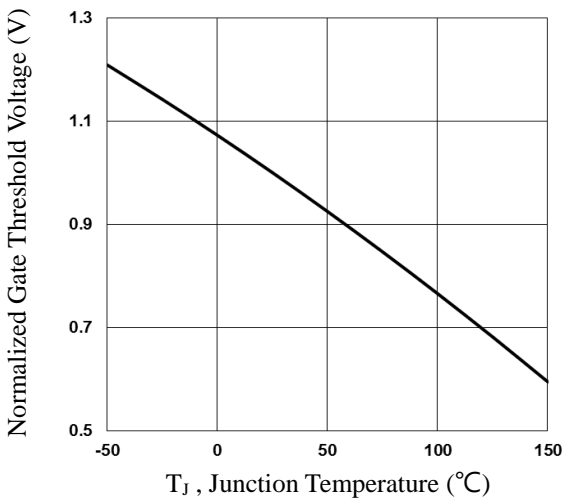
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=39A., R<sub>G</sub>=25Ω, Starting T<sub>J</sub>=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.



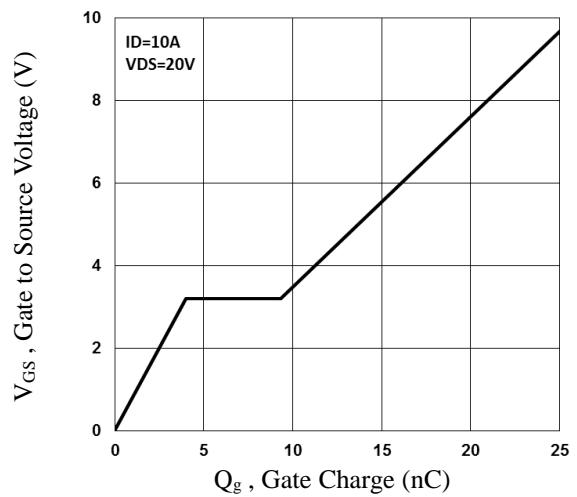
**Fig.1 Continuous Drain Current vs.  $T_c$**



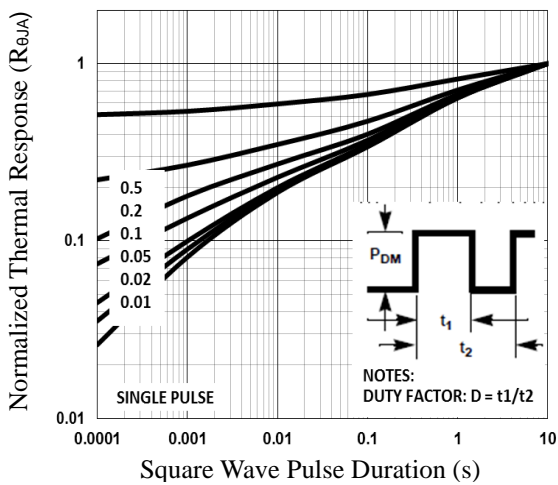
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



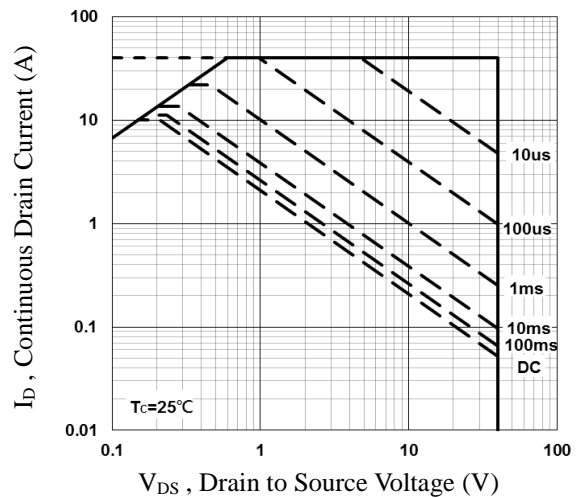
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



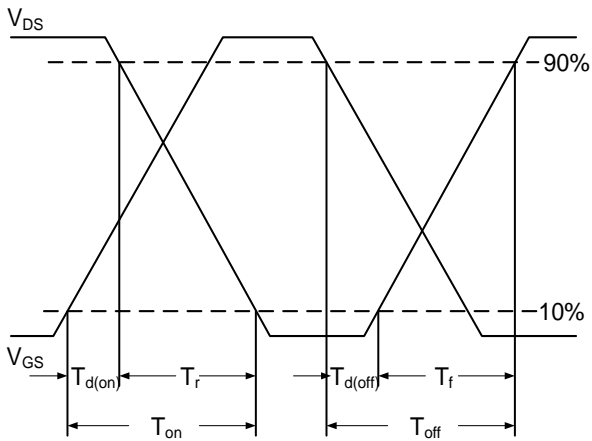
**Fig.4 Gate Charge Waveform**



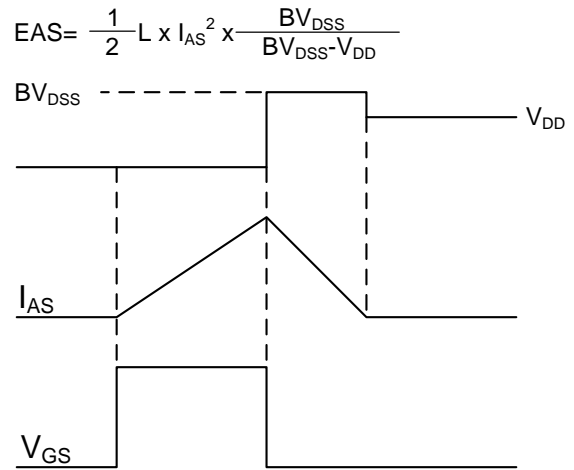
**Fig.5 Normalized Transient Impedance**



**Fig.6 Maximum Safe Operation Area**

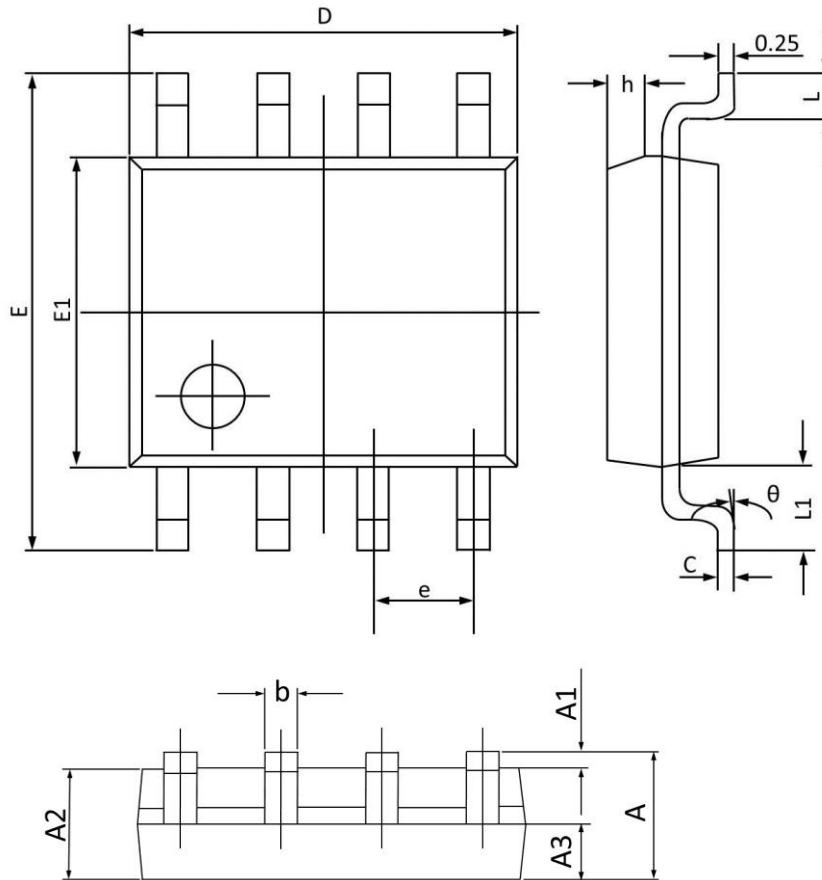


**Fig.7 Switching Time Waveform**



**Fig.8 EAS Waveform**

## SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.250	1.650	0.049	0.065
A3	0.500	0.700	0.020	0.028
b	0.380	0.510	0.015	0.020
c	0.170	0.260	0.007	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.020
L	0.400	0.800	0.016	0.031
L1	1.050(BSC)		0.041(BSC)	
$\theta$	0°	8°	0°	8°